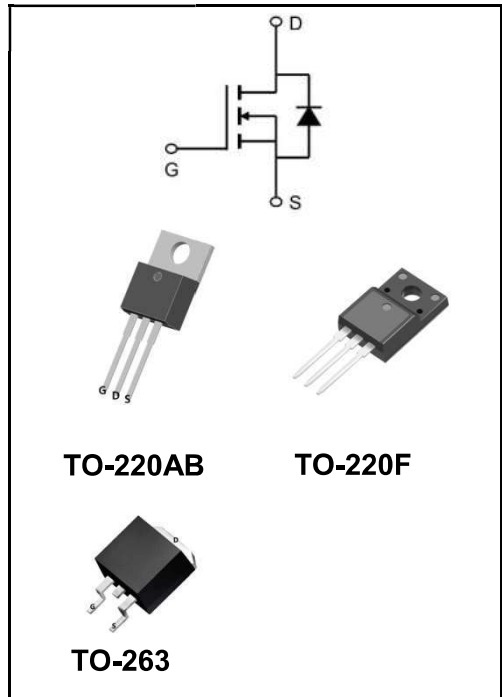


60V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

$I_D$	90A
$V_{DSS}$	60V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 7.0mΩ (Type:5.8 mΩ)



Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

Product Specification Classification

Part Number	Package	Marking	Pack
YFW90N06AT	TO-220AB	YFW 90N06AT XXXXX	1000PCS/box
YFW90N06AF	TO-220F	YFW 90N06AF XXXXX	1000PCS/box
YFW90N06AS	TO-263	YFW 90N06AS XXXXX	800PCS/Reel

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate - Source Voltage	$V_{GS}$	±20	V
Continuous drain current <sup>1)</sup>	$I_D$	90	A
Pulsed drain current <sup>2)</sup>	$I_{DM}$	320	A
Diode forward current	$I_S$	37	A
Pulsed source current	$I_{SP}$	210	A
Power dissipation	$P_D$	108	W
Single pulsed avalanche energy <sup>3)</sup>	$E_{AS}$	205.4	mJ
Operation and storage temperature	$T_{STG}, T_J$	-55 to +150	°C
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.4	°C/W
Thermal Resistance, Junction-to-Ambient <sup>4)</sup>	$R_{\theta JA}$	62.5	°C/W

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	<b>V(BR)DSS</b>	60	64	-	<b>V</b>
Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V$	<b>I<sub>DSS</sub></b>	-	-	1.0	<b>μA</b>
Gate to Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	<b>I<sub>GSS</sub></b>	-	-	±100	<b>nA</b>
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	<b>V<sub>GS(th)</sub></b>	2.0	3.0	4.0	<b>V</b>
Static Drain-Source on-Resistance note	$V_{GS}=10V, I_D=30A$	<b>R<sub>DS(ON)</sub></b>	-	5.8	7.0	<b>mΩ</b>
Input Capacitance	$V_{DS}=30V$ $V_{GS}=0V$ $f=1.0MHz$	<b>C<sub>iss</sub></b>	-	4136	-	<b>pF</b>
Output Capacitance		<b>C<sub>oss</sub></b>	-	286	-	
Reverse Transfer Capacitance		<b>C<sub>rss</sub></b>	-	257	-	
Total Gate Charge	$V_{DS}=30V$ $I_D=30A$ $V_{GS}=10V$	<b>Q<sub>g</sub></b>	-	90	-	<b>nC</b>
Gate-Source Charge		<b>Q<sub>gs</sub></b>	-	9	-	
Gate-Drain("Miller") Charge		<b>Q<sub>gd</sub></b>	-	18	-	
Turn-on delay time	$V_{DS}=30V, I_D=30A$ $R_G=1.8\Omega, V_{GS}=10V$	<b>t<sub>d(on)</sub></b>	-	9	-	<b>ns</b>
Turn-on Rise Time		<b>T<sub>r</sub></b>	-	7	-	
Turn-Off Delay Time		<b>t<sub>d(OFF)</sub></b>	-	40	-	
Turn-Off Fall Time		<b>t<sub>f</sub></b>	-	15	-	
Maximum Continuous Drain to Source Diode Forward Current		<b>I<sub>S</sub></b>	-	-	90	<b>A</b>
Maximum Pulsed Drain to Source Diode Forward Current		<b>I<sub>SM</sub></b>			320	<b>A</b>
Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	<b>V<sub>SD</sub></b>	-	-	1.2	<b>V</b>
Body Diode Reverse Recovery Time	$I_S=30A, dI/dt=100A/\mu s$	<b>t<sub>rr</sub></b>	-	33	-	<b>ns</b>
Body Diode Reverse Recovery Charge		<b>Q<sub>rr</sub></b>	-	46	-	<b>nC</b>

Note :

- 1、 The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、 The test cond  $\cong$  300us duty cycle  $\cong$  2%, duty cycle ition is  $T_J=25^\circ C, V_{DD}=35V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=21A$
- 4、 The power dissipation is limited by  $175^\circ C$  junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

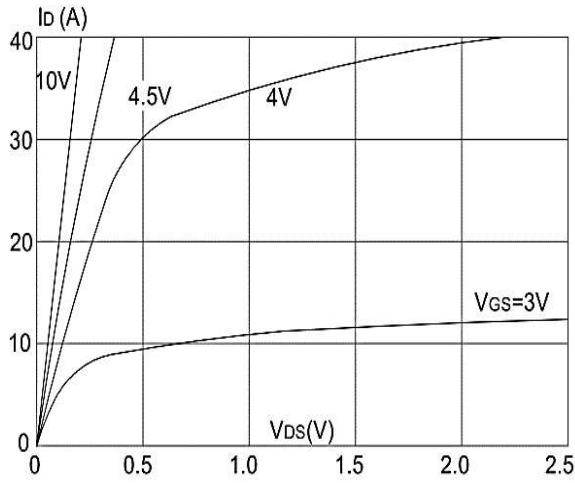


Figure 1: Output Characteristics

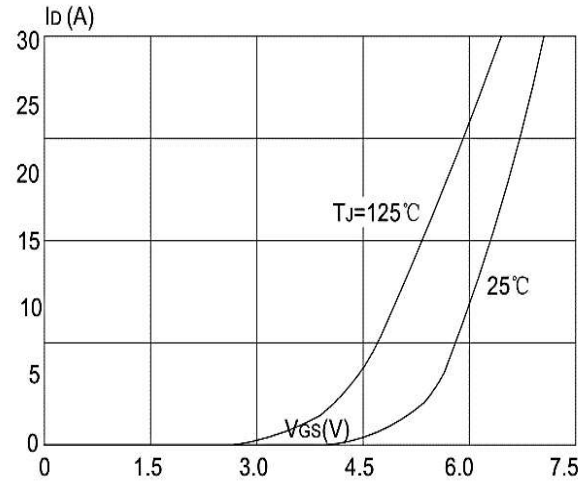


Figure 2: Typical Transfer Characteristics

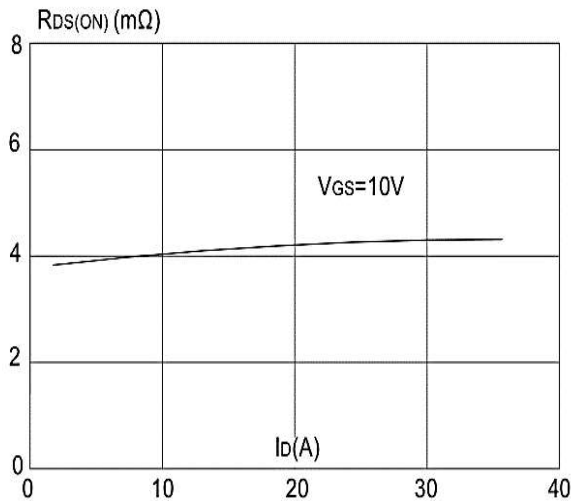


Figure 3: On-resistance vs. Drain Current

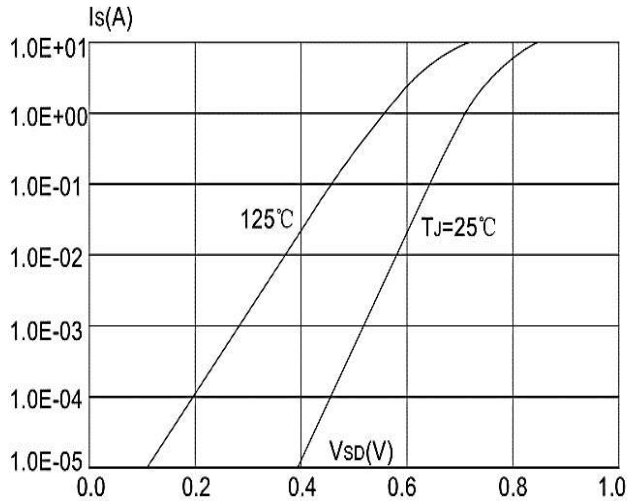


Figure 4: Body Diode Characteristics

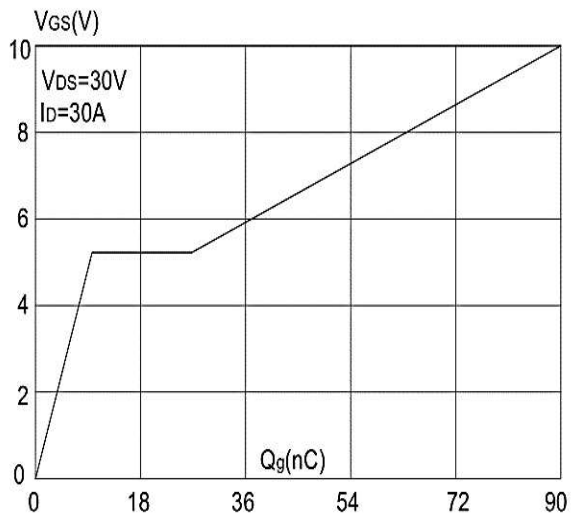


Figure 5: Gate Charge Characteristics

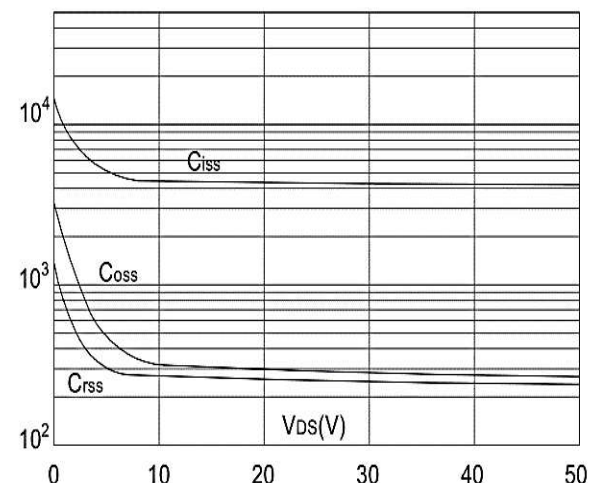
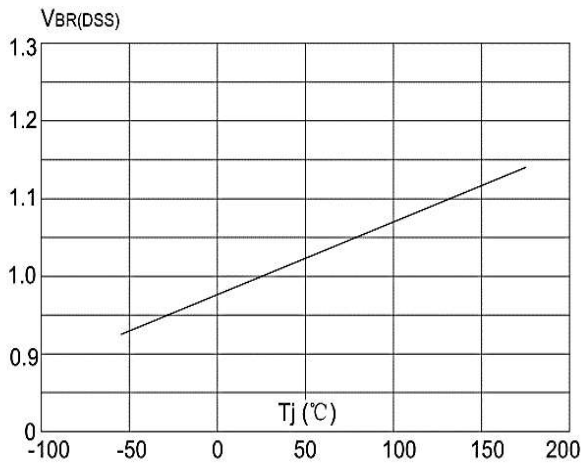
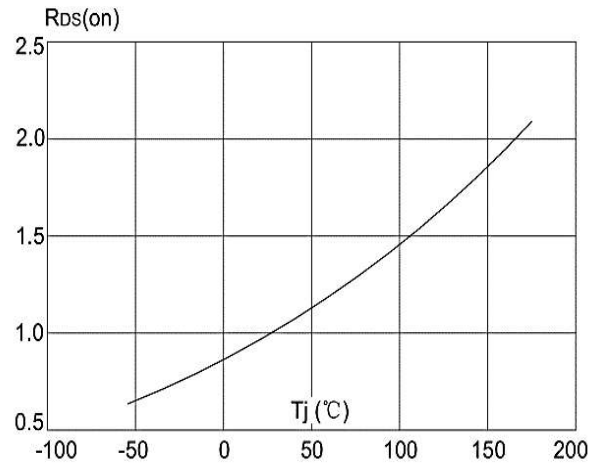


Figure 6: Capacitance Characteristics

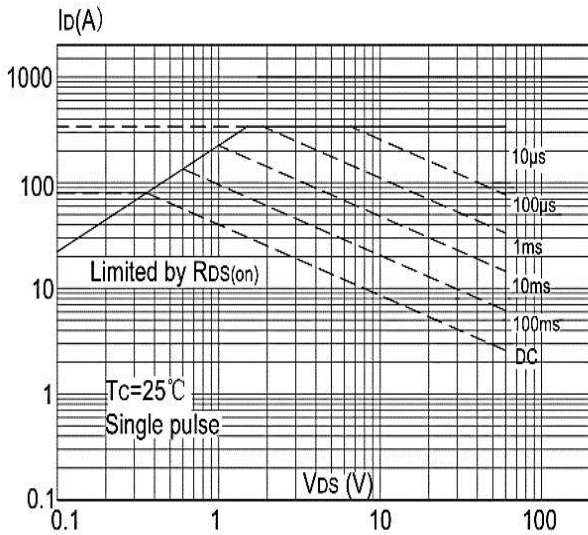
**Ratings and Characteristic Curves**



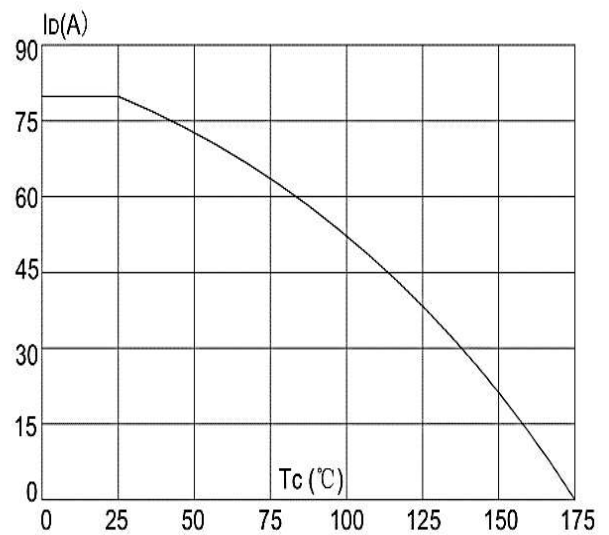
**Figure 7: Normalized Breakdown Voltage vs Junction Temperature**



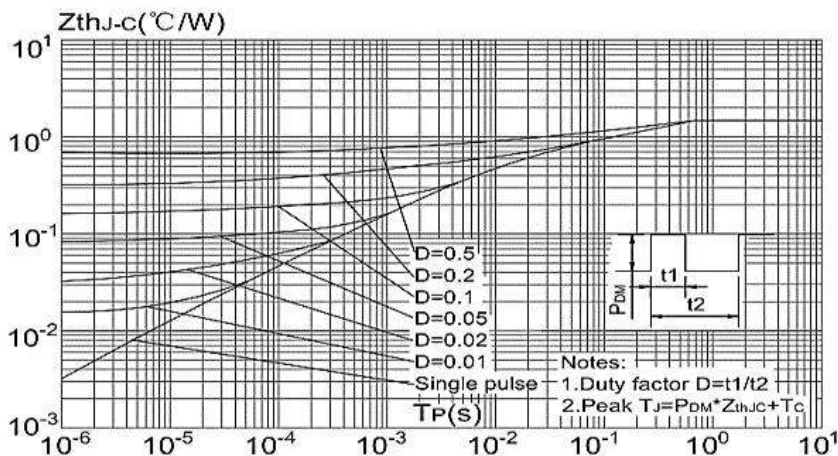
**Figure 8: Normalized on Resistance vs. Junction Temperature**



**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature**



**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien**

Package Outline Dimensions Millimeters

TO-220AB

	Dim.	Min.	Max.
	A	10.15	10.35
	B	2.65	2.95
	C	3.70	3.90
	D	28.5	29.5
	E	1.30	1.45
	F	6.35	6.55
	G	2.9	3.3
	H	15.0	16.0
	I	0.38	0.42
	J	4.45	4.55
	K	1.25	1.35
	L	Typ 5.08	
	M	Typ 2.54	
	N	3.1	3.3
O	0.76	0.84	
All Dimensions in millimeter			

TO-220F

	Dim.	Min.	Max.
	A	9.95	10.25
	B	2.95	3.25
	C	1.25	1.45
	D	12.95	13.25
	E	0.50	0.65
	F	3.1	3.3
	G	1.30	1.45
	H	Typ 2.54	
	I	Typ 5.08	
	J	4.60	4.75
	K	2.50	2.65
	L	6.35	6.55
	M	15.4	16.0
	N	2.75	3.05
O	0.48	0.52	
P	0.76	0.84	
All Dimensions in millimeter			

Package Outline Dimensions Millimeters

TO-263

	Dim.	Min.	Max.
	A	10.1	10.2
	B	7.4	7.6
	C	1.3	1.5
	D	0.55	0.75
	E	5.0	6.0
	F	1.4	1.6
	G	0.78	0.86
	H	1.2	1.3
	I	Typ2.54	
	J	8.4	8.6
	K	4.45	4.55
	L	1.25	1.35
	M	0.02	0.1
	N	2.4	2.8
O	0.36	0.40	
All Dimensions in millimeter			